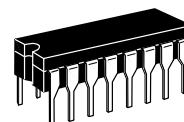


**CMOS MSI**  
**Quad R-S Latches**

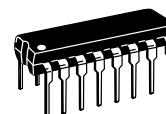
The MC14043B and MC14044B quad R-S latches are constructed with MOS P-channel and N-channel enhancement mode devices in a single monolithic structure. Each latch has an independent Q output and set and reset inputs. The Q outputs are gated through three-state buffers having a common enable input. The outputs are enabled with a logical "1" or high on the enable input; a logical "0" or low disconnects the latch from the Q outputs, resulting in an open circuit at the Q outputs.

- Double Diode Input Protection
- Three-State Outputs with Common Enable
- Outputs Capable of Driving Two Low-power TTL Loads or One Low-power Schottky TTL Load Over the Rated Temperature Range
- Supply Voltage Range = 3.0 Vdc to 18 Vdc

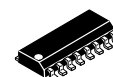
**MC14043B**  
**MC14044B**



**L SUFFIX**  
CERAMIC  
CASE 620



**P SUFFIX**  
PLASTIC  
CASE 648

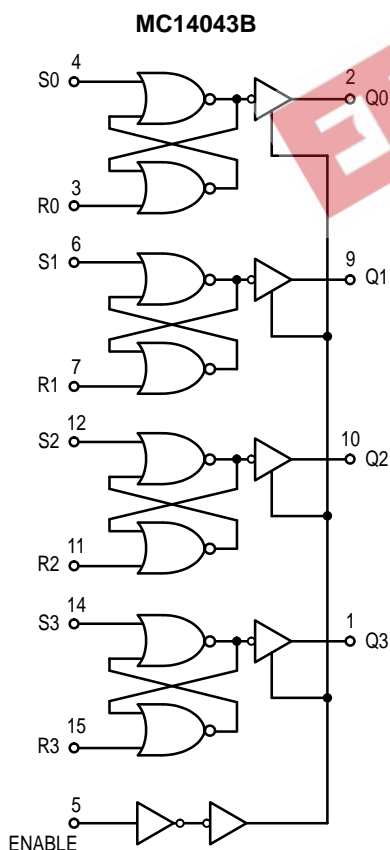


**D SUFFIX**  
SOIC  
CASE 751B

**ORDERING INFORMATION**

MC14XXXBCP Plastic  
MC14XXXBCL Ceramic  
MC14XXXBD SOIC

T<sub>A</sub> = -55° to 125°C for all packages.

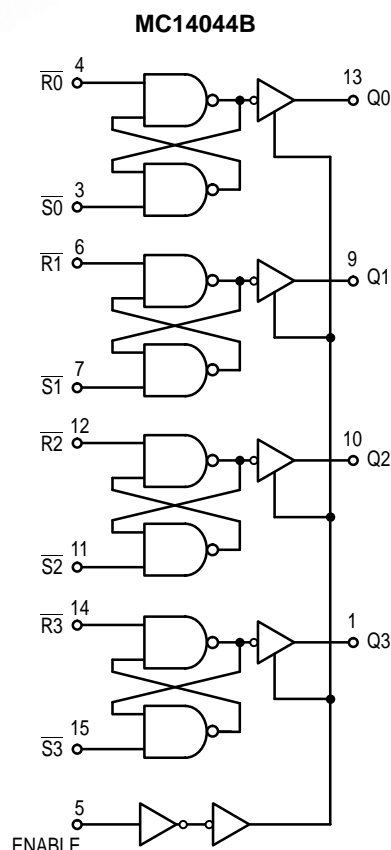


V<sub>DD</sub> = PIN 16  
V<sub>SS</sub> = PIN 8  
NC = PIN 13

**TRUTH TABLE**

S	R	E	Q
X	X	0	High Impedance
0	0	1	No Change
0	1	1	0
1	0	1	1
1	1	1	1

X = Don't Care



V<sub>DD</sub> = PIN 16  
V<sub>SS</sub> = PIN 8  
NC = PIN 2

**TRUTH TABLE**

S	R	E	Q
X	X	0	High Impedance
0	0	1	0
0	1	1	1
1	0	1	0
1	1	1	No Change

X = Don't Care



**ELECTRICAL CHARACTERISTICS** (Voltages Referenced to V<sub>SS</sub>)

Characteristic	Symbol	V <sub>DD</sub> Vdc	- 55°C		25°C			125°C		Unit
			Min	Max	Min	Typ #	Max	Min	Max	
Output Voltage V <sub>in</sub> = V <sub>DD</sub> or 0  V <sub>in</sub> = 0 or V <sub>DD</sub>	"0" Level V <sub>OL</sub>	5.0	—	0.05	—	0	0.05	—	0.05	Vdc
		10	—	0.05	—	0	0.05	—	0.05	
		15	—	0.05	—	0	0.05	—	0.05	
	"1" Level V <sub>OH</sub>	5.0	4.95	—	4.95	5.0	—	4.95	—	Vdc
		10	9.95	—	9.95	10	—	9.95	—	
		15	14.95	—	14.95	15	—	14.95	—	
Input Voltage (V <sub>O</sub> = 4.5 or 0.5 Vdc) (V <sub>O</sub> = 9.0 or 1.0 Vdc) (V <sub>O</sub> = 13.5 or 1.5 Vdc)  (V <sub>O</sub> = 0.5 or 4.5 Vdc) (V <sub>O</sub> = 1.0 or 9.0 Vdc) (V <sub>O</sub> = 1.5 or 13.5 Vdc)	"0" Level V <sub>IL</sub>	5.0	—	1.5	—	2.25	1.5	—	1.5	Vdc
		10	—	3.0	—	4.50	3.0	—	3.0	
		15	—	4.0	—	6.75	4.0	—	4.0	
	"1" Level V <sub>IH</sub>	5.0	3.5	—	3.5	2.75	—	3.5	—	Vdc
		10	7.0	—	7.0	5.50	—	7.0	—	
		15	11	—	11	8.25	—	11	—	
Output Drive Current (V <sub>OH</sub> = 2.5 Vdc) (V <sub>OH</sub> = 4.6 Vdc) (V <sub>OH</sub> = 9.5 Vdc) (V <sub>OH</sub> = 13.5 Vdc)  (V <sub>OL</sub> = 0.4 Vdc) (V <sub>OL</sub> = 0.5 Vdc) (V <sub>OL</sub> = 1.5 Vdc)	Source I <sub>OH</sub>	5.0	- 3.0	—	- 2.4	- 4.2	—	- 1.7	—	mAdc
		5.0	- 0.64	—	- 0.51	- 0.88	—	- 0.36	—	
		10	- 1.6	—	- 1.3	- 2.25	—	- 0.9	—	
		15	- 4.2	—	- 3.4	- 8.8	—	- 2.4	—	
	Sink I <sub>OL</sub>	5.0	0.64	—	0.51	0.88	—	0.36	—	mAdc
		10	1.6	—	1.3	2.25	—	0.9	—	
15		4.2	—	3.4	8.8	—	2.4	—		
Input Current	I <sub>in</sub>	15	—	± 0.1	—	± 0.00001	± 0.1	—	± 1.0	μAdc
Input Capacitance (V <sub>in</sub> = 0)	C <sub>in</sub>	—	—	—	—	5.0	7.5	—	—	pF
Quiescent Current (Per Package)	I <sub>DD</sub>	5.0	—	1.0	—	0.002	1.0	—	30	μAdc
		10	—	2.0	—	0.004	2.0	—	60	
		15	—	4.0	—	0.006	4.0	—	120	
Total Supply Current**† (Dynamic plus Quiescent, Per Package) (C <sub>L</sub> = 50 pF on all outputs all buffers switching)	I <sub>T</sub>	5.0	I <sub>T</sub> = (0.58 μA/kHz) f + I <sub>DD</sub>							μAdc
		10	I <sub>T</sub> = (1.15 μA/kHz) f + I <sub>DD</sub>							
		15	I <sub>T</sub> = (1.73 μA/kHz) f + I <sub>DD</sub>							
Three-State Output Leakage Current	I <sub>TL</sub>	15	—	± 0.1	—	± 0.0001	± 0.1	—	± 3.0	μAdc

#Data labelled "Typ" is not to be used for design purposes but is intended as an indication of the IC's potential performance.

\*\*The formulas given are for the typical characteristics only at 25°C.

†To calculate total supply current at loads other than 50 pF:

$$I_T(C_L) = I_T(50 \text{ pF}) + (C_L - 50) Vfk$$

where: I<sub>T</sub> is in μA (per package), C<sub>L</sub> in pF, V = (V<sub>DD</sub> - V<sub>SS</sub>) in volts, f in kHz is input frequency, and k = 0.004.

\* Maximum Ratings are those values beyond which damage to the device may occur.

†Temperature Derating: Plastic "P and D/DW" Packages: - 7.0 mW/°C From 65°C To 125°C  
Ceramic "L" Packages - 12 mW/°C From 100°C To 125°C

**MAXIMUM RATINGS\*** (Voltages Referenced to  $V_{SS}$ )

Symbol	Parameter	Value	Unit
$V_{DD}$	DC Supply Voltage	- 0.5 to + 18.0	V
$V_{in}, V_{out}$	Input or Output Voltage (DC or Transient)	- 0.5 to $V_{DD} + 0.5$	V
$I_{in}, I_{out}$	Input or Output Current (DC or Transient), per Pin	$\pm 10$	mA
$P_D$	Power Dissipation, per Package†	500	mW
$T_{stg}$	Storage Temperature	- 65 to + 150	°C
$T_L$	Lead Temperature (8-Second Soldering)	260	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation,  $V_{in}$  and  $V_{out}$  should be constrained to the range  $V_{SS} \leq (V_{in} \text{ or } V_{out}) \leq V_{DD}$ . Unused inputs must always be tied to an appropriate logic voltage level (e.g., either  $V_{SS}$  or  $V_{DD}$ ). Unused outputs must be left open.

\* Maximum Ratings are those values beyond which damage to the device may occur.

† Temperature Derating:

Plastic "P and D/DW" Packages: - 7.0 mW/°C From 65°C To 125°C

Ceramic "L" Packages: - 12 mW/°C From 100°C To 125°C

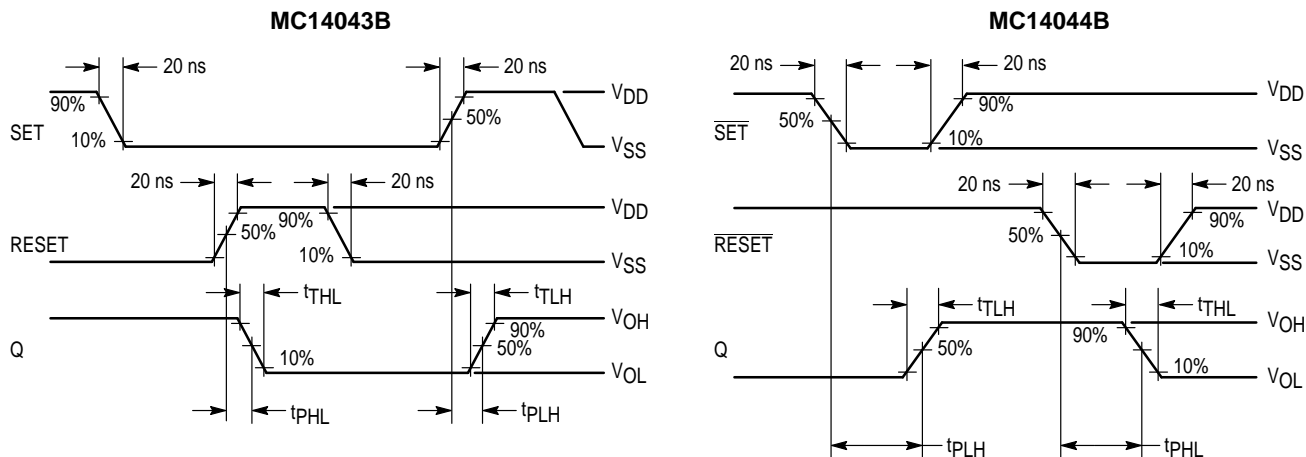
**SWITCHING CHARACTERISTICS\*** ( $C_L = 50 \text{ pF}, T_A = 25^\circ\text{C}$ )

Characteristic	Symbol	$V_{DD}$ Vdc	Min	Typ #	Max	Unit
Output Rise Time $t_{TLH} = (1.35 \text{ ns/pF}) C_L + 32.5 \text{ ns}$ $t_{TLH} = (0.60 \text{ ns/pF}) C_L + 20 \text{ ns}$ $t_{TLH} = (0.40 \text{ ns/pF}) C_L + 20 \text{ ns}$	$t_{TLH}$	5.0 10 15	— — —	100 50 40	200 100 80	ns
Output Fall Time $t_{THL} = (1.35 \text{ ns/pF}) C_L + 32.5 \text{ ns}$ $t_{THL} = (0.60 \text{ ns/pF}) C_L + 20 \text{ ns}$ $t_{THL} = (0.40 \text{ ns/pF}) C_L + 20 \text{ ns}$	$t_{THL}$	5.0 10 15	— — —	100 50 40	200 100 80	ns
Propagation Delay Time $t_{PLH} = (0.90 \text{ ns/pF}) C_L + 130 \text{ ns}$ $t_{PLH} = (0.36 \text{ ns/pF}) C_L + 57 \text{ ns}$ $t_{PLH} = (0.26 \text{ ns/pF}) C_L + 47 \text{ ns}$ $t_{PHL} = (0.90 \text{ ns/pF}) C_L + 130 \text{ ns}$ $t_{PHL} = (0.90 \text{ ns/pF}) C_L + 57 \text{ ns}$ $t_{PHL} = (0.26 \text{ ns/pF}) C_L + 47 \text{ ns}$	$t_{PLH}$ $t_{PHL}$	5.0 10 15 5.0 10 15	— — — — — —	175 75 60 175 75 60	350 175 120 350 175 120	ns
Set, $\overline{\text{Set}}$ Pulse Width	$t_W$	5.0 10 15	200 100 70	80 40 30	— — —	ns
Reset, $\overline{\text{Reset}}$ Pulse Width	$t_W$	5.0 10 15	200 100 70	80 40 30	— — —	ns
Three-State Enable/Disable Delay	$t_{PLZ}$ , $t_{PHZ}$ , $t_{PZL}$ , $t_{PZH}$	5.0 10 15	— — —	150 80 55	300 160 110	ns

\* The formulas given are for the typical characteristics only at 25°C.

#Data labelled "Typ" is not to be used for design purposes but is intended as an indication of the IC's potential performance.

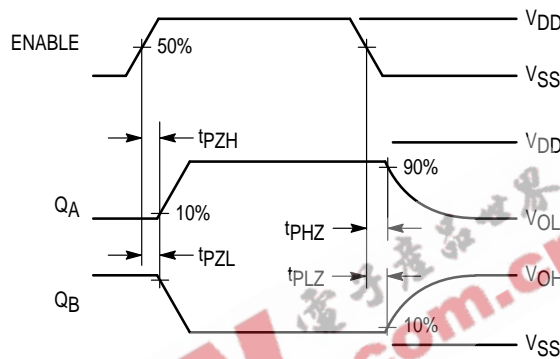
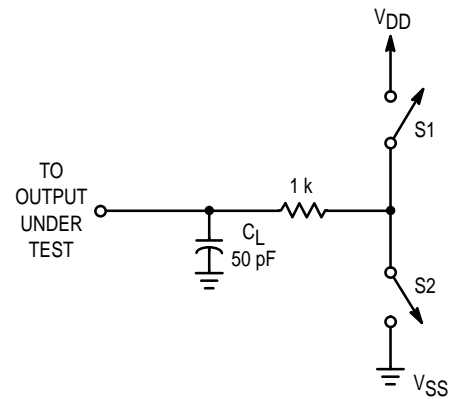
**AC WAVEFORMS**



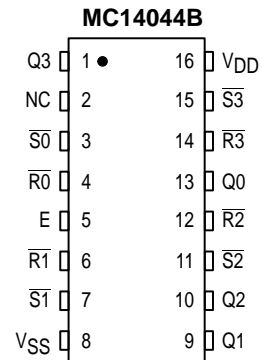
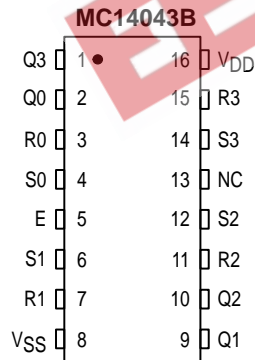
### THREE-STATE ENABLE/DISABLE DELAYS

#### Set, Reset, Enable, and Switch Conditions for 3-State Tests

Test	Enable	S1	S2	Q	MC14043B		MC14044B	
					S	R	$\bar{S}$	$\bar{R}$
tPZH		Open	Closed	A	V <sub>DD</sub>	V <sub>SS</sub>	V <sub>SS</sub>	V <sub>DD</sub>
tPZL		Closed	Open	B	V <sub>SS</sub>	V <sub>DD</sub>	V <sub>DD</sub>	V <sub>SS</sub>
tPHZ		Open	Closed	A	V <sub>DD</sub>	V <sub>SS</sub>	V <sub>SS</sub>	V <sub>DD</sub>
tPLZ		Closed	Open	B	V <sub>SS</sub>	V <sub>DD</sub>	V <sub>DD</sub>	V <sub>SS</sub>



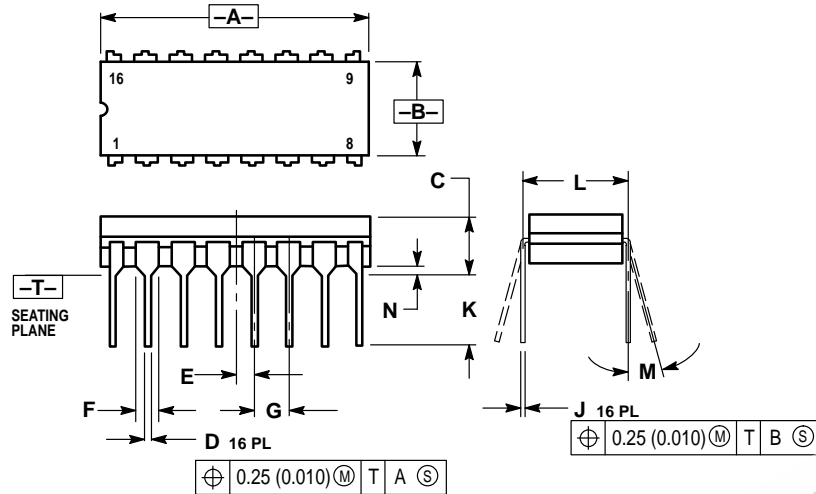
#### PIN ASSIGNMENT



NC = NO CONNECTION

## OUTLINE DIMENSIONS

### L SUFFIX CERAMIC DIP PACKAGE CASE 620-10 ISSUE V

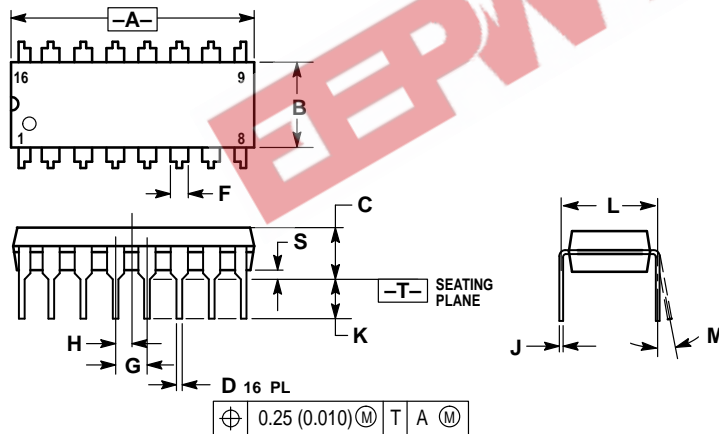


**NOTES:**

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION L TO CENTER OF LEAD WHEN FORMED PARALLEL.
4. DIMENSION F MAY NARROW TO 0.76 (0.030) WHERE THE LEAD ENTERS THE CERAMIC BODY.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.750	0.785	19.05	19.93
B	0.240	0.295	6.10	7.49
C	—	0.200	—	5.08
D	0.015	0.020	0.39	0.50
E	0.050 BSC		1.27 BSC	
F	0.055	0.065	1.40	1.65
G	0.100 BSC		2.54 BSC	
H	0.008	0.015	0.21	0.38
K	0.125	0.170	3.18	4.31
L	0.300 BSC		7.62 BSC	
M	0°	15°	0°	15°
N	0.020	0.040	0.51	1.01

### P SUFFIX PLASTIC DIP PACKAGE CASE 648-08 ISSUE R



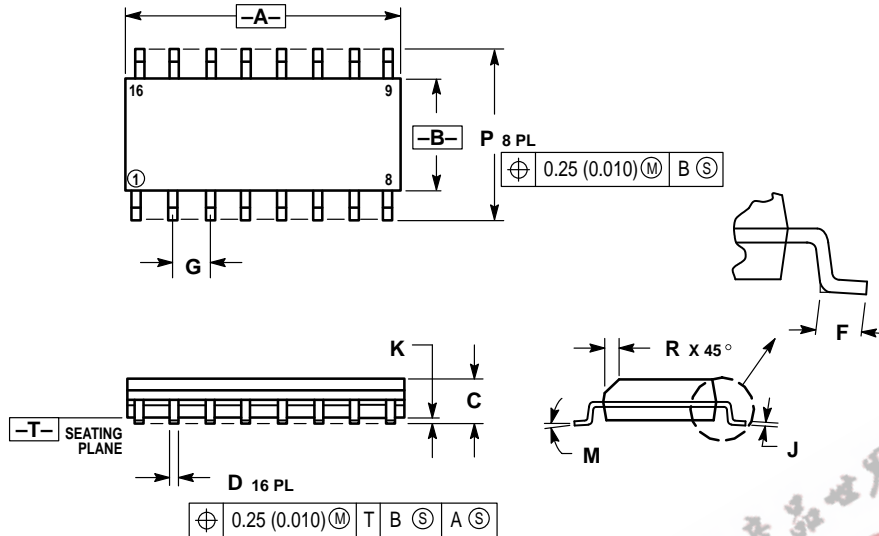
**NOTES:**

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION L TO CENTER OF LEADS WHEN FORMED PARALLEL.
4. DIMENSION B DOES NOT INCLUDE MOLD FLASH.
5. ROUNDED CORNERS OPTIONAL.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.740	0.770	18.80	19.55
B	0.250	0.270	6.35	6.85
C	0.145	0.175	3.69	4.44
D	0.015	0.021	0.39	0.53
F	0.040	0.70	1.02	1.77
G	0.100 BSC		2.54 BSC	
H	0.050 BSC		1.27 BSC	
J	0.008	0.015	0.21	0.38
K	0.110	0.130	2.80	3.30
L	0.295	0.305	7.50	7.74
M	0°	10°	0°	10°
S	0.020	0.040	0.51	1.01

## OUTLINE DIMENSIONS

### D SUFFIX PLASTIC SOIC PACKAGE CASE 751B-05 ISSUE J



**NOTES:**

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	9.80	10.00	0.386	0.393
B	3.80	4.00	0.150	0.157
C	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27 BSC		0.050 BSC	
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
M	0°	7°	0°	7°
P	5.80	6.20	0.229	0.244
R	0.25	0.50	0.010	0.019

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MC14043B/D

